Code No.: R22EC301PC

[Time: 3 Hours]

**R22** 

H.T.No.

8 R

[Max. Marks: 60]

## CMR ENGINEERING COLLEGE: : HYDERABAD UGC AUTONOMOUS

## II-B.TECH-I-Semester End Examinations (Regular) - December- 2024 ELECTRONIC DEVICES AND CIRCUITS (ECE)

	T		1	
1	<b>Note:</b> This question paper contains two parts A and B.			
	Part A is compulsory which carries 10 marks. Answer all questions in Part A.			
		Part B consists of 5 Units. Answer any one full question from each unit. Each question		
		· ·		
	(	carries 10 marks and may have a, b, c as sub questions.		
		$\underline{PART-A} \tag{10}$	Marks)	
	1. a)	Explain how the reverse saturation current of a P-N junction diode varies with	[1M]	
		temperature.		
	b)	Give the expressions for ripple factor and efficiency for full wave rectifier.	[1M]	
	c)	Define Early Effect.	[1M]	
	d)	Mention the advantages and disadvantages of self-bias method.	[1M]	
	e)	Mention the working principle of varactor diode.	[1M]	
	f)	List out the differences between JFET and MOSFET.	Control of the contro	
			[1M]	
	g)	Write the expressions for the h-parameters of a transistor under CE configuration.	[1M]	
	h)	List out Comparison of transistor amplifiers of CE,CB and CC.	[1M]	
	i)	What are the different types of FETs?	[1M]	
	j)	Why the input impedance of FET is higher than BJT?	[1M]	
		PART-B (50	Marks)	
	2.	Explain PN junction diode in forward and reverse bias conditions with suitable diagrams.	[10M]	
	2.	OR	[TOTAL]	
	2		[10]	
	3.	Derive the expressions for ripple factor and efficiency of a Half wave rectifier.	[10M]	
	4	Draw the aircuit discress of an NBN junction transister in CE configuration and avalain	[10]/[]	
	4.	Draw the circuit diagram of an NPN junction transistor in CE configuration and explain	[10M]	
		the input and output characteristics.		
		OR		
	5.a)	What is the need for biasing? Explain self biasing method in BJT.	[7M]	
	b)	Write about Thermal runaway.	[3M]	
	6.	Illustrate the construction and operation of n-channel JFET with neat diagrams.	[10M]	
		OR		
	7.	Explain the working of Zener diode and its V-I characteristics. What is the sufficient	[10M]	
		condition for regulation?		
		**************************************		
	8.	Draw the circuit diagram of Common Emitter (CE) amplifier and derive expression for	[10M]	
		voltage gain, current gain, input impedance and output admittance using approximate		
		model.		
		OR		
	0		[10M]	
	9.	Explain the determination of H-parameters of a two port network.	[TOIVI]	
	10.	Draw the circuit diagram of common source (CS) amplifier and derive expression for	[10M]	
		voltage gain input impedance and output impedance.		
		OR		
	11	Explain the operation and draw drain and transfer characteristics of depletion type	[10M]	
	11.		[TOIVI]	
		MOSFET.		

\*\*\*\*\*\*